Electric field induced strong localization of electrons on solid hydrogen surface: possible applications to quantum computing

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Two-dimensional electron system on the liquid helium surface is one of the leading candidates for constructing large analog quantum computers (P.M. Platzman and M.I. Dykman, Science 284, 1967 (1999)). Similar electron systems on the surfaces of solid hydrogen or solid neon may have some important advantages with respect to electrons on liquid helium in quantum computing applications, such as larger state separation ΔE, absence of propagating capillary waves (or ripplons), smaller vapor pressure, etc. As a result, it may operate at higher temperatures. Surface roughness is the main hurdle to overcome in building a realistic quantum computer using these states. Electric field induced strong localization of surface electrons is shown to be a convenient tool to characterize surface roughness.

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Quantum computers may provide an enormous gain in the computation rate due to high parallelism of multi-qubit quantum evolution [1]. They are viewed as a system of N two-level interacting quantum systems (qubits) that evolve in time under the action of some time-dependent Hamiltonian (computer program). The computer operation is based on a controlled series of qubit couplings together with one-qubit rotations.

Two-dimensional electron system on the liquid helium surface is one of the leading candidates for constructing large analog quantum computers [2]. It consists of a set of electrons $N \sim 10^9$ trapped in vacuum in the image states on the surface of a liquid helium film. The ground and the first excited state of an electron in the image potential may represent 0 and 1 state of a qubit. The electron states (qubits) and electron-electron interactions can be easily manipulated by external electric fields and resonant microwave radiation. On the other hand, these electrons are sufficiently isolated from the outside world: they are coupled to it only through the irregularities of the helium film, such as capillary waves and the substrate defects, and through the collisions with vapor molecules. Thus, these two-dimensional electron systems can behave as quantum computers with many qubits. Unfortunately, the operation temperature of such a computer must be below $10^{-2}K$ [2] which is caused by small quantum state separation $\Delta E \sim 8K$, thermal excitation of propagating capillary waves (or ripplons) on the liquid He surface, large He vapor pressure at higher temperatures, etc.

In this Letter we are going to show that similar two-dimensional electron systems on the surfaces of solid hydrogen or neon may have some important advantages with respect to electrons on liquid helium in quantum computing applications. Since surface roughness is the main hurdle to overcome in building a realistic quantum computer using these states, it is very important to develop reliable tools for its characterization. Electric field induced strong localization of electrons on solid hydrogen surface observed in the experiment is suggested as such a reliable tool to characterize roughness of solid hydrogen or solid neon surface.

Most of the experimental and theoretical work on two-dimensional electron states above the dielectric surfaces with $(\epsilon - 1) << 1$ has been done for the case of liquid helium [3]. In the simplest model, the interaction potential ϕ for an electron near the surface of such a dielectric depends only on the electrostatic image force, and on the external electric field E, which is normal to the surface and is necessary for the electron confinement near the surface:

$$\phi(z) = -e^2(\epsilon - 1)/(4z(\epsilon + 1)) + eEz = -Qe^2/z + eEz \tag{1}$$

for $z > 0$, and $\phi(z) = V_0$ for $z < 0$, where the z axis is normal to the surface, and V_0 is the surface potential barrier. If $V_0 \to \infty$ one obtains the electron energy spectrum:

$$E_n = -Q^2me^4/(2\hbar^2n^2) + eE < z_n > +p^2/(2m) \tag{2}$$

The first term in this expression gives the exact solution for $E = 0$. The second term is the first-order correction for a non-zero confining field, where the average distance of electrons from the surface in the nth energy level is $< z_n >= 3n^2\hbar^2/(2me^2Q)$. This correction provides an extremely convenient way of fine-tuning

the energy spectrum with electric signals. In [2] it was proposed to use patterned electrodes to adjust separately the field E acting on each electron (qubit), so that one can address each qubit with a correctly chosen frequency of a microwave driving field. The maximum density of electrons on the dielectric surface is determined by the average external confining field: $n \leq E/(4\pi e)$ [3]. Density values of the order of 10^9 cm^{-2} are routinely observed which correspond to a reasonable (from the point of view of current state of lithographical techniques) ~ 300 nm spacing between individual electrons (and, hence, individual electrodes necessary to address each of the electrons separately). The last term in (2) corresponds to free electron's motion parallel to the surface.

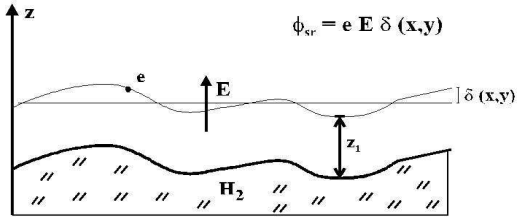

FIG. 1. Surface topography induces variations in the random potential relief ($H_{sr} = eE\delta(x,y)$) seeing by the electron in its lateral motion under the applied external confining field E.

Similar two-dimensional electron layers have been observed on the surface of liquid and solid hydrogen and neon [3]. Resonant absorption of light for $1 \rightarrow 2$ and $1 \rightarrow 3$ transitions in the spectrum of electrons levitating above the surfaces of solid hydrogen and neon has been reported and the frequencies of these transitions have been measured as a function of the confining electric field [4,5]. Because of approximately three times larger values of Q for solid hydrogen and neon, the electrons levitate closer (at a distance of $\sim 25\mathring{A}$) to the surface and have an order of magnitude larger separation ΔE between quantum energy states. Nevertheless, like electrons on liquid helium surface, they have pretty high mobility $\mu \sim 10^4 cm^2/Vs$ [6] limited by surface roughness. Coupling to surface roughness ($H_{sr} = eE\delta$, where δ represents the surface height variations) is supposed to determine the relaxation time T from the n=2 to n=1 state for a moving electron. It is essential to keep T as large as possible for a successful operation of a quantum computer. Although the photoresonance linewidth ($\Delta\nu \sim 3 \times 10^{10}$ Hz) measured in [4,5] is not sufficiently narrow for quantum computer operation, it was most probably caused by inhomogeneous broadening due to variations in height of the samples and crystal orientation. Simple estimate of a homogeneous line width for electrons on atomically flat crystal surface gives six orders of magnitude smaller linewidth of $\Delta\nu \sim \omega_{12}^3 d_{12}^2/(3\hbar c^3) \sim 10^4$ Hz, where ω_{12} and d_{12} are the frequency and the average dipole moment of the $1 \rightarrow 2$ transition. This value is just slightly larger than the value expected for electrons on liquid helium surface. Thus, ability to grow high quality atomically flat surfaces of solid hydrogen or solid neon would be of critical importance for building a quantum computer using surface electron states. Most of the other properties of electron systems on solid hydrogen and neon give them substantial advantages with respect to electrons on liquid helium in quantum computing applications. Larger separation ΔE between the energy states, much smaller vapor pressure at low temperatures, and the absence of propagating capillary waves (or ripplons) may allow a quantum computer operation at sufficiently higher temperatures around 4K. This would make a quantum computer based on surface electron states much more feasible from the technological point of view.

Surface electrons have been previously suggested as a tool to characterize surface roughness of solid hydrogen films prepared by quench condensation on a glass substrate at 1.5K [7]. Surface electron conductivity has been studied as a function of temperature, and thermal-activation-type dependencies have been observed for the "very rough" samples obtained. The measured activation energy of the order of 10K or more has been suggested as an indicator of surface quality of the hydrogen samples used. This method may not be appropriate for higher quality samples since surface roughness may itself be a function of temperature in the state of thermal equilibrium. The idea of alternative isothermic surface roughness measurements based on Anderson localization is illustrated in Fig.1. Variation of external confining field E applied to an electron localized in the ground state over a rough hydrogen surface leads to linear variations in the random potential relief ($H_{sr} = eE\delta(x,y)$) seeing by the electron in its lateral motion. For a lateral roughness scale smaller than the electron wavelength ($\lambda = 2\pi\hbar/(2mkT)^{1/2} \sim 40$ nm at T=10K) we may expect a classic case of Anderson localization [8] at a sufficiently high confining field strength.

According to the measurements of electron mobility on high quality crystals of solid hydrogen [6], at 13.4K the main contributions to surface electron scattering come from the collisions with hydrogen molecules in the vapor phase, and from the collisions with surface defects. The value of the electron mobility $\mu = 7500 cm^2/Vs$ measured at 13.4K is above the "minimal metallic mobility" value μ_{min} that corresponds to the electron free propagation length l of the order of the electron wavelength λ: the electron mobility may be written as

$$\mu = e\tau/m = \frac{\pi e\hbar}{mkT}\frac{l}{\lambda} \qquad (3)$$

where τ is the free propagation time. At $l/\lambda \sim 1$ and

T=13.4K the minimal metallic mobility value is equal to $\mu_{min} \approx 3100 cm^2/Vs$. These numbers show that although the surface electrons are supposed to have the diffusive type of conductivity, they are not far from strong localization. Increase in scattering by the surface defects due to application of higher confining electric field should cause such a localization.

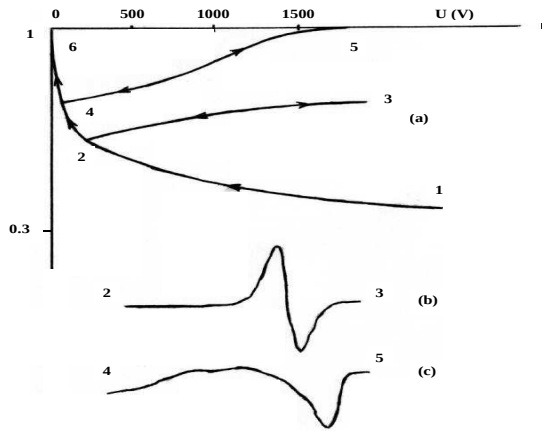

FIG. 2. (a) Radio frequency absorption of the electron layer on top of a 1 mm thick hydrogen crystal measured as a function of the bottom electrode potential. The data obtained on the way from the point (1) to points (2), (4), and (6) correspond to irreversible escape of the electrons from the surface with the electron density determined by $n = E/(4\pi e)$. The drop in absorption upon the confining field increase on the way from (2) to (3), or from (4) to (5) was reversible with the surface electron density unchanged over the duration of the measurements. (b,c) Photoresonance $1 \rightarrow 2$ transitions detected in the electron layer on the way (2-3) (b) and (4-5) (c). Optical signal is proportional to the derivative of the optical absorption at $\lambda = 84.3 \mu m$.

An exponential drop in surface electron conductivity under the applied confining electric field has been indeed observed in the experiment. The method of conductivity measurements has been discussed in detail in [4]. A 1.0 mm thick solid hydrogen crystal was grown on the polished sapphire substrate from the liquid hydrogen phase at the triple point. A two-dimensional electron layer levitating above the hydrogen crystal surface was created at a temperature of 13.4K by a pulse of electric current through a tungsten filament located above the crystal. Two electrodes separated by 2.3 mm produced a uniform confining electric field perpendicular to the crystal surface. The upper electrode was grounded. The lower (aluminum) electrode was deposited on the sapphire by vacuum sputtering. The electrodes were 30 mm in diameter and were large enough so that the fringe fields could be neglected near the center of the hydrogen surface. The lower electrode was separated by a narrow gap into two parts that were connected in parallel to a superconducting LC circuit with a resonant frequency of 94 kHz. Appearance of an electron layer on the hydrogen surface led to a decrease of the LC circuit's Q-factor (initially equaled to $Q \approx 1000$), and to the decrease of the output signal proportional to the non-resonant radio-frequency absorption of the electron layer. The absorption of the electron layer (proportional to its conductivity which is determined by the electrons density and the mobility of individual electrons in the layer) was recorded while scanning the potential of the lower electrode (see Fig.2). Electrons completely charged the hydrogen surface at point (1) when the pulse of current through the filament occurred. The data obtained on the way from the point (1) to points (2), (4), and (6) correspond to irreversible escape of the electrons from the surface with the electron density determined by $n = E/(4\pi e)$. The drop in absorption upon the confining field increase on the way from (2) to (3), or from (4) to (5) was reversible with the average surface electron density unchanged over the duration of the measurements. This drop in absorption is mainly caused by the increase in the electron scattering by surface defects due to larger scattering cross-sections of the topographical defects at larger confining electric fields. In principle, some electron redistribution over the crystal surface may also happen, although this effect is supposed to be small in the geometry of the experiment. The surface area covered by electrons may only change by a few percents due to the fact that the horizontal component of the confining field exists only near the edges of the closely spaced top and bottom electrodes (and in the narrow gap between the electrodes and the walls of the experimental chamber). Moreover, such a redistribution of electrons would cause an opposite effect on the absorption signal due to an increase in the electron density.

Thus, a signal proportional to the electron mobility was measured as a function of the confining electric field. While the behavior of electron absorption on the way (4-5) clearly exhibits evidences of strong localization, the measurements (2-3) performed at higher electron density do not show any sign of localization within the measurements range. This behavior may be attributed to the two-dimensional screening of the lateral potential relief by the conductive electron layer. According to [9], the screening parameter of a non-degenerate 2D electron gas equals to $S = 2\pi e^2 n/(kT)$, which gives the values of $S_{45}^{-1} = 36$ nm and $S_{23}^{-1} = 8$ nm for the electron densities of $n_{45} = 3.6 \times 10^8 cm^{-2}$ and $n_{23} = 1.6 \times 10^9 cm^{-2}$ in the measurements (4-5) and (2-3) respectively. It seems reasonable to assume that the screening would strongly affect the character of electron's conductivity when the screening length becomes comparable to the characteristic size of surface defects. Thus, the numbers obtained for the screening length indicate the characteristic lateral

size (in the 8 - 36 nm range) of the surface roughness seen by the electrons. The fact that this lateral size is smaller than the electron's wavelength justifies the applicability of the Anderson localization model to our experimental situation.

The data of the transport measurements were also supported by the simultaneous measurements of photoresonance $1 \rightarrow 2$ transition in the electron spectrum (2). These data are presented in Fig.2(b,c). The optical signal proportional to the derivative of the optical absorption at $\lambda = 84.3\mu m$ was measured using 50V modulation of the bottom electrode potential. A substantial asymmetric photoresonance line broadening can be seen as a direct result of Anderson localization. This is a natural result since each localized electron is supposed to see different local topographical environment.

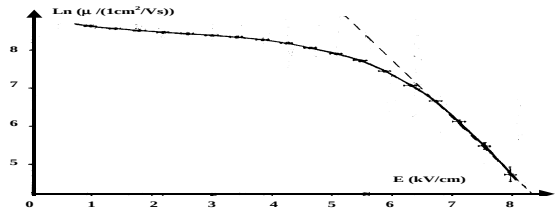

FIG. 3. The data of the measurements (4-5) from Fig.2 plotted as a logarithm of electrons mobility versus confining electric field E. These data clearly show the transition from the diffusive to activation-type of conductivity of the surface electron layer.

Fig.3 represents the data obtained in the measurements (4-5) plotted as a logarithm of electrons mobility versus confining electric field E. These data clearly show the transition from the diffusive to the activation-type of conductivity of the surface electron layer ($\sigma \sim exp(-E_c/kT)$), with the conductivity threshold E_c that depends linearly on the confining field. This linear dependence is exactly the behavior one would expect from the model shown in Fig.1. Thus, the average height variation of the hydrogen surface may be recovered as $\delta = \frac{kT}{e}\frac{d(ln\mu)}{dE} \sim 16$ nm. The developed technique may be used in the growth and characterization of higher quality crystals of hydrogen and neon that is necessary in quantum computing applications. The confining field strength necessary to induce strong localization may serve as a convenient indicator of surface quality.

The observed electric field induced Anderson localization may also be treated as a simple example of qubit coupling and de- coupling using external electric signals, which is also very important from the point of view of building a large quantum computer. The degree of overlap of the electrons wave functions may be conveniently adjusted by modifying the confining electric field.

In conclusion, it was pointed out that two-dimensional electron systems on the surfaces of solid hydrogen or solid neon may have some important advantages with respect to electrons on liquid helium in quantum computing applications. Such quantum computers may be operational at higher temperatures around 4K if a sufficient smoothness of solid hydrogen or solid neon surfaces may be achieved. Electric field induced strong localization of surface electrons is shown to be a reliable tool to characterize surface roughness.

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